

# **PMV160UPVL** Datasheet



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DiGi Electronics Part Number PMV160UPVL-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMV160UPVL

Description MOSFET P-CH 20V 1.2A TO236AB

Detailed Description P-Channel 20 V 1.2A (Ta) 335mW (Ta) Surface Mou

nt TO-236AB



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## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PMV160UPVL	Nexperia USA Inc.
Series:	Product Status:
-	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	1.2A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
1.8V, 4.5V	210mOhm @ 1.2A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
950mV @ 250μA	4 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±8V	365 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	335mW (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
TO-236AB	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
PMV160	

## **Environmental & Export classification**

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



## PMV160UP

# 20 V, 1.2 A P-channel Trench MOSFET Rev. 2 — 6 December 2011

Product data sheet

#### **Product profile**

#### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- 1.8 V R<sub>DSon</sub> rated
- Very fast switching

Trench MOSFET technology

#### 1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-	-1.2	Α
Static charact	teristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$		-	170	210	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

## **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source	3	
3	D	drain	1	G 017aaa257



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20 V, 1.2 A P-channel Trench MOSFET

## 3. Ordering information

#### Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV160UP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

## 4. Marking

#### Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PMV160UP	NH%

[1] % = placeholder for manufacturing site code

## 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		<b>3</b> , ( ,				
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-1.2	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	-0.8	Α
I <sub>DM</sub>	peak drain current	$T_{amb} = 25  ^{\circ}C$ ; single pulse; $t_p \le 10  \mu s$		-	-4	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	335	mW
			<u>[1]</u>	-	480	mW
		T <sub>sp</sub> = 25 °C		-	2170	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode					
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-0.5	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

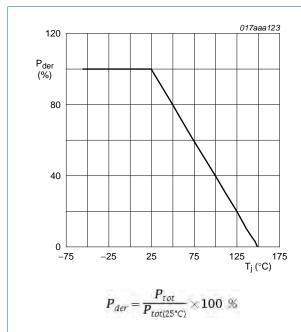
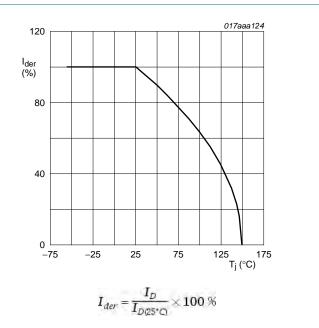


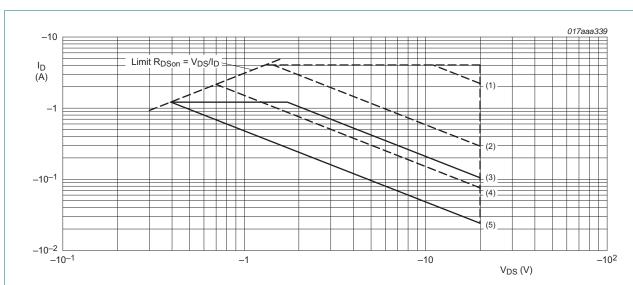
Fig 1. Normalized total power dissipation as a function of junction temperature



ig 2. Normalized continuous drain current as a function of junction temperature

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#### 20 V, 1.2 A P-channel Trench MOSFET



I<sub>DM</sub> = single pulse

- (1)  $t_p = 1 \text{ ms}$
- (2)  $t_p = 10 \text{ ms}$
- (3) DC;  $T_{sp} = 25 \, ^{\circ}\text{C}$
- (4)  $t_p = 100 \text{ ms}$
- (5) DC;  $T_{amb} = 25 \, ^{\circ}C$ ; drain mounting pad 6 cm<sup>2</sup>

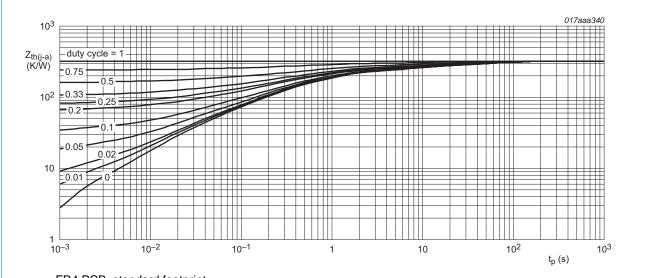
Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 6. Thermal characteristics

Table 6. Thermal characteristics

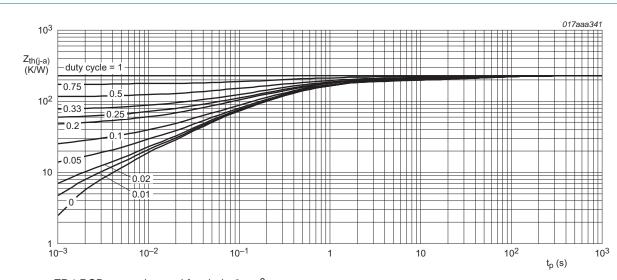
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
un() a)	thermal resistance	in free air [1] [2]	-	325	374	K/W	
	from junction to ambient		[2]	-	227	260	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	50	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 7. Characteristics

Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
		$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
Boon	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$	-	170	210	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 150 \text{ °C}$	-	265	328	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -1.1 \text{ A}; T_j = 25 \text{ °C}$	-	210	270	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -0.5 \text{ A}; T_j = 25 \text{ °C}$	-	280	380	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; I_{D} = -1.2 \text{ A}; T_{j} = 25 ^{\circ}\text{C}$	-	3.7	-	S
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -1 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	3.3	4	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	1	-	nC
$Q_{GD}$	gate-drain charge		-	0.5	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -10 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	365	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	42	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	30	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $V_{GS}$ = -4.5 V; $R_{G(ext)}$ = 6 $\Omega$ ;	-	7	-	ns
t <sub>r</sub>	rise time	$T_j = 25 ^{\circ}\text{C};  I_D = -1 ^{\circ}\text{A}$	-	26	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	35	-	ns
t <sub>f</sub>	fall time		-	17	-	ns
Source-di	rain diode					
$V_{SD}$	source-drain voltage	$I_S = -0.5 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	-0.7	-1.2	V

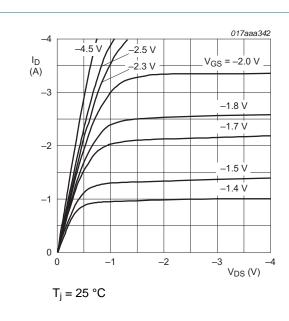
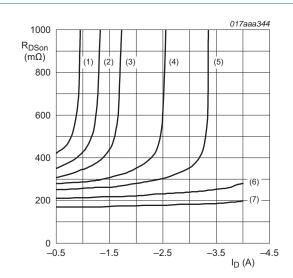


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$ 

(1)  $V_{GS} = -1.4 \text{ V}$ 

(2)  $V_{GS} = -1.5 \text{ V}$ 

(3)  $V_{GS} = -1.6 \text{ V}$ 

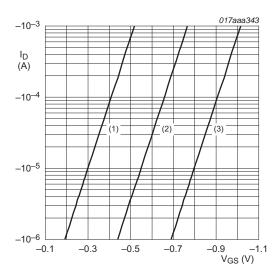
(4)  $V_{GS} = -1.8 \text{ V}$ 

(5)  $V_{GS} = -2.0 \text{ V}$ 

(6)  $V_{GS} = -2.5 \text{ V}$ 

 $(7) V_{GS} = -4.5 V$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



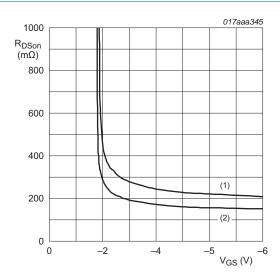
 $T_{j} = 25 \, ^{\circ}\text{C}; \, V_{DS} = -5 \, \text{V}$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



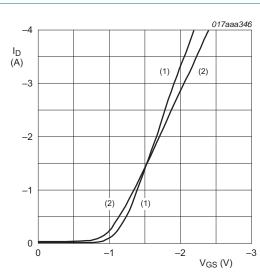
 $I_D = -2.5 A$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_j = 25 \, ^{\circ}C$$

(2) 
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

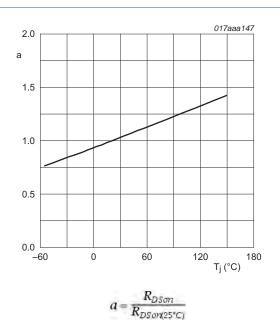
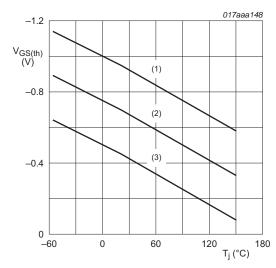


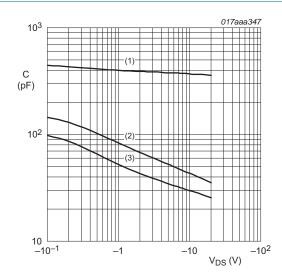
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



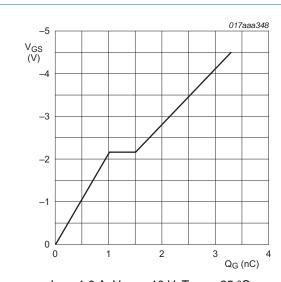
 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 $I_D$  = -1.0 A;  $V_{DS}$  = -10 V;  $T_{amb}$  = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

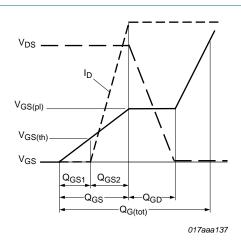
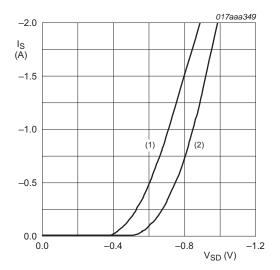


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ 

(1)  $T_j = 150 \, ^{\circ}C$ 

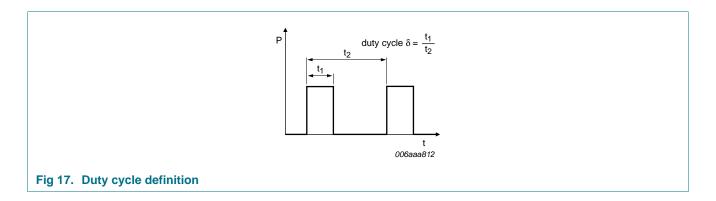
(2)  $T_i = 25 \, ^{\circ}C$ 

Fig 16. Source current as a function of source-drain voltage; typical values

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## 8. Test information



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## 9. Package outline

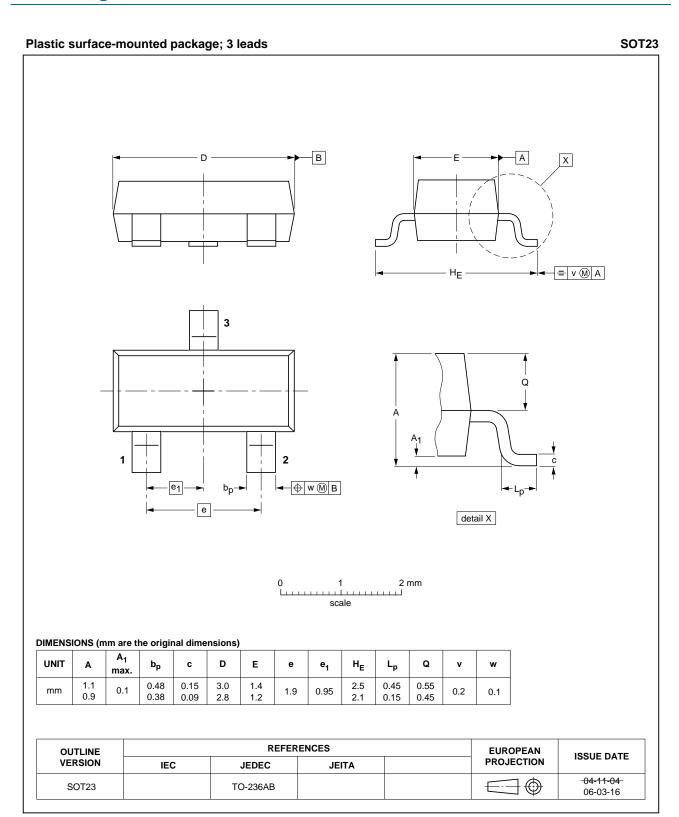
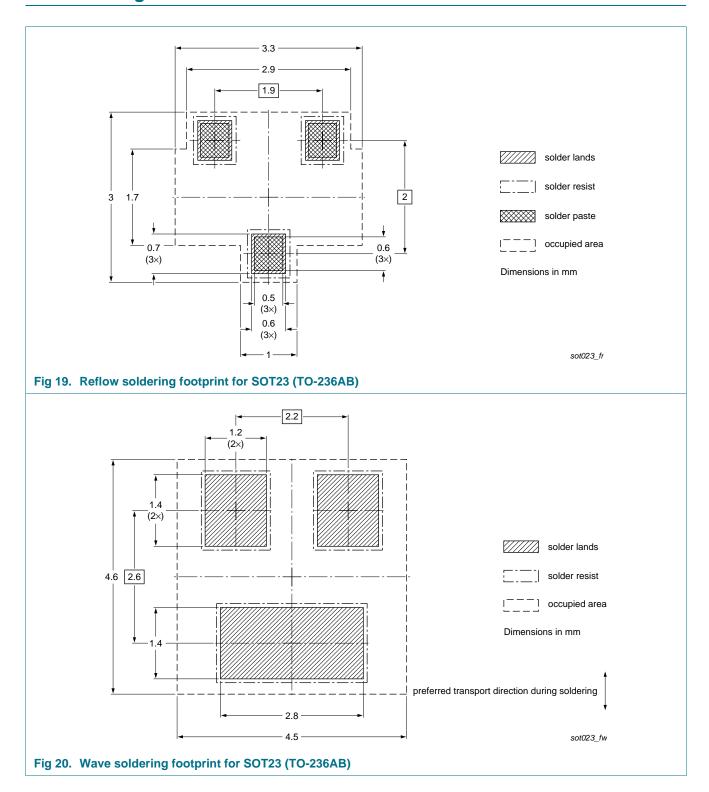


Fig 18. Package outline SOT23 (TO-236AB)

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## 10. Soldering



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## 11. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMV160UP v.2	20111206	Product data sheet	-	PMV160UP v.1
Modifications:	<ul> <li>7 "Characteristics"</li> </ul>	: V <sub>GSth</sub> condition is correc	cted	
PMV160UP v.1	20110907	Product data sheet	-	-

#### 12. Legal information

#### 12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions'
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